

FDA38N30
N-Channel MOSFET
300V, 38A, 0.085Ω

Features

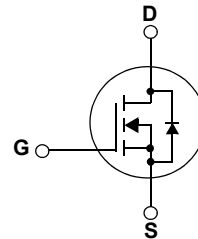
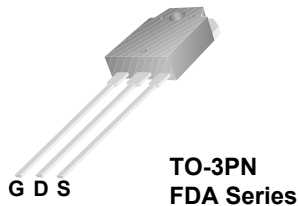
- $R_{DS(on)} = 0.07\Omega$ (Typ.) @ $V_{GS} = 10V, I_D = 19A$
- Low gate charge (typical 60 nC)
- Low C_{rss} (typical 60 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- ESD Improved capability
- RoHS Compliant



Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | FDA38N30 | Unit |
|----------------|--|---|------------------|
| V_{DSS} | Drain to Source Voltage | 300 | V |
| V_{GSS} | Gate to Source Voltage | ± 30 | V |
| I_D | Drain Current | -Continuous ($T_C = 25^\circ\text{C}$) | 38 |
| | | -Continuous ($T_C = 100^\circ\text{C}$) | 22 |
| I_{DM} | Drain Current - Pulsed (Note 1) | 150 | A |
| E_{AS} | Single Pulsed Avalanche Energy (Note 2) | 1200 | mJ |
| I_{AR} | Avalanche Current (Note 1) | 38 | A |
| E_{AR} | Repetitive Avalanche Energy (Note 1) | 31 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 4.5 | V/ns |
| P_D | Power Dissipation | ($T_C = 25^\circ\text{C}$) | 312 |
| | | - Derate above 25°C | 2.5 |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +150 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | 300 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | Min. | Max. | Unit |
|-----------------|---|------|------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | - | 0.4 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta CS}$ | Thermal Resistance, Case-to-Sink | 0.24 | - | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | - | 40 | $^\circ\text{C}/\text{W}$ |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|----------|---------|-----------|------------|----------|
| FDA38N30 | FDA38N30 | TO-3PN | - | - | 30 |

Electrical Characteristics T_C = 25°C unless otherwise noted

| Symbol | Parameter | Conditions | Min. | Typ. | Max | Units |
|---|--|---|------|------|-------|-------|
| Off Characteristics | | | | | | |
| BV _{DSS} | Drain to Source Breakdown Voltage | I _D = 250μA, V _{GS} = 0V, T _C = 25°C | 300 | - | - | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 250μA, Referenced to 25°C | - | 0.3 | - | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 300V, V _{GS} = 0V | - | - | 1 | μA |
| | | V _{DS} = 240V, T _C = 125°C | - | - | 10 | |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V, V _{DS} = 0V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 3.0 | - | 5.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = 10V, I _D = 19A | - | 0.07 | 0.085 | Ω |
| g _{FS} | Forward Transconductance | V _{DS} = 20V, I _D = 19A (Note 4) | - | 6.3 | - | S |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} = 25V, V _{GS} = 0V f = 1MHz | - | 2600 | - | pF |
| C _{oss} | Output Capacitance | | - | 500 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | | - | 60 | - | pF |
| Q _{g(tot)} | Total Gate Charge at 10V | V _{DS} = 240V, I _D = 38A V _{GS} = 10V (Note 4, 5) | - | 60 | - | nC |
| Q _{gs} | Gate to Source Gate Charge | | - | 17 | - | nC |
| Q _{gd} | Gate to Drain "Miller" Charge | | - | 28 | - | nC |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 150V, I _D = 38A R _G = 25Ω, V _{GS} = 10V (Note 4, 5) | - | 53 | 69 | ns |
| t _r | Turn-On Rise Time | | - | 110 | 143 | ns |
| t _{d(off)} | Turn-Off Delay Time | | - | 118 | 153 | ns |
| t _f | Turn-Off Fall Time | | - | 54 | 70 | ns |
| Drain-Source Diode Characteristics | | | | | | |
| I _S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | 38 | A |
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | - | - | 150 | A |
| V _{SD} | Drain to Source Diode Forward Voltage | V _{GS} = 0V, I _{SD} = 38A | - | - | 1.4 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0V, I _{SD} = 38A | - | 315 | - | ns |
| Q _{rr} | Reverse Recovery Charge | dI _F /dt = 100A/μs (Note 4) | - | 4.0 | - | μC |

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1.7mH, I_{AS} = 38A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 38A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

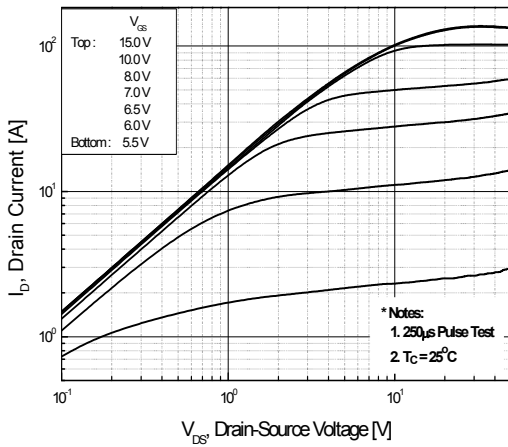


Figure 2. Transfer Characteristics

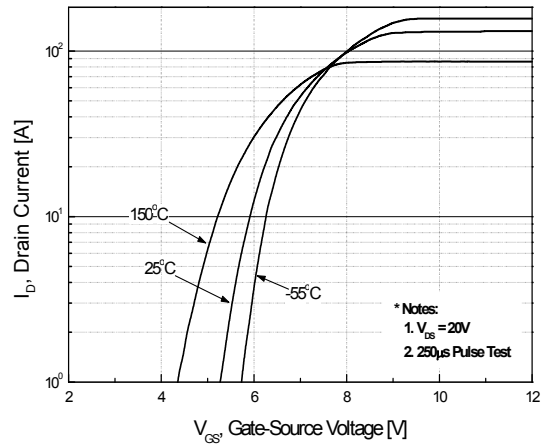


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

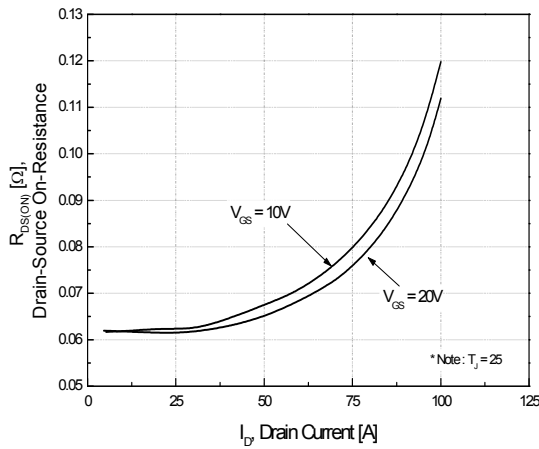


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

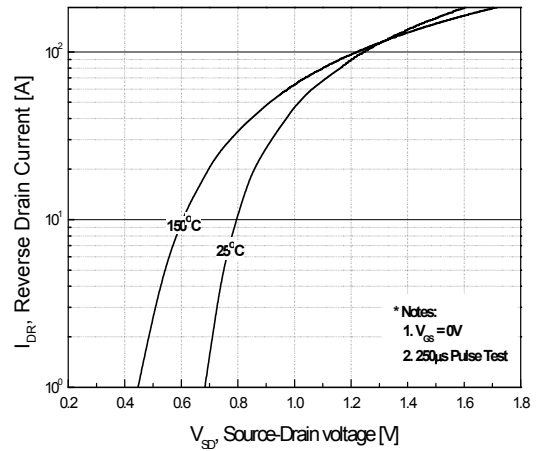


Figure 5. Capacitance Characteristics

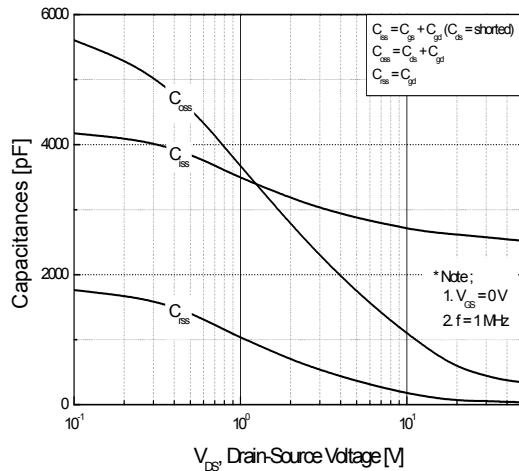
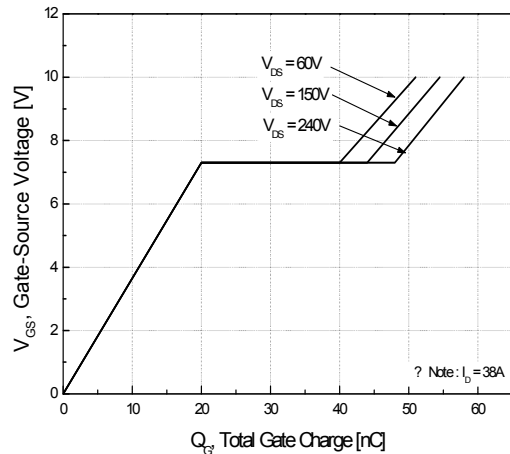


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

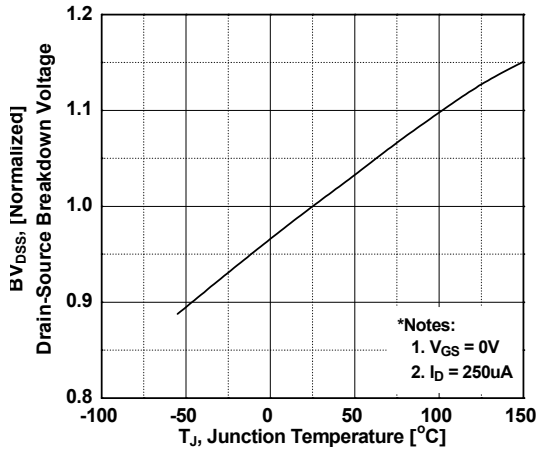


Figure 8. On-Resistance Variation vs. Temperature

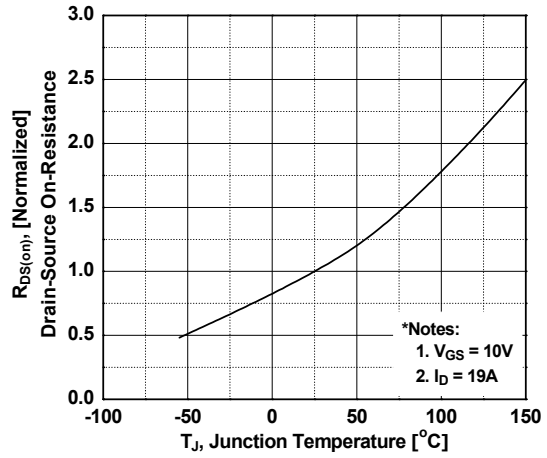


Figure 9. Maximum Safe Operating Area

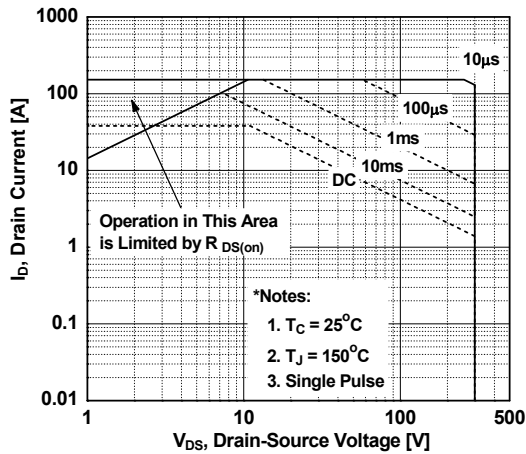


Figure 10. Maximum Drain Current vs. Case Temperature

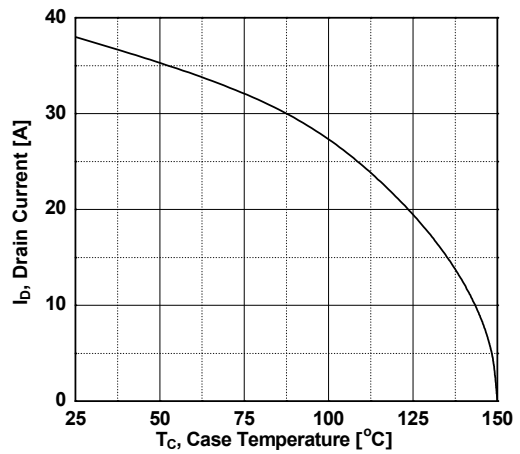
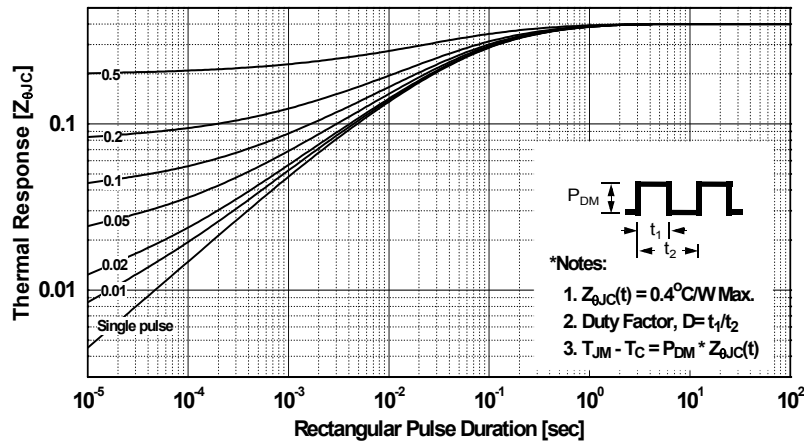
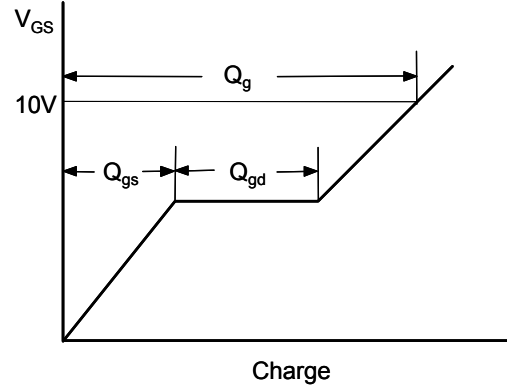
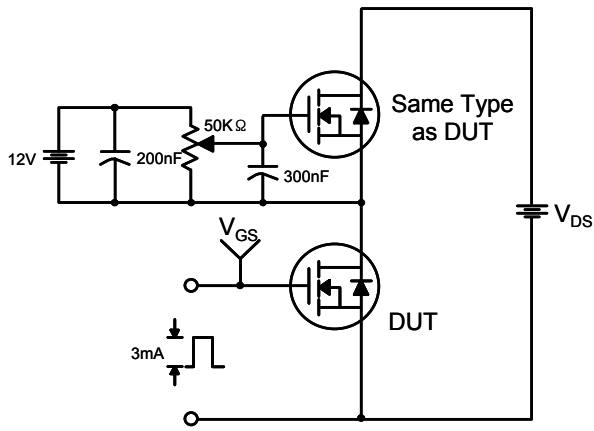


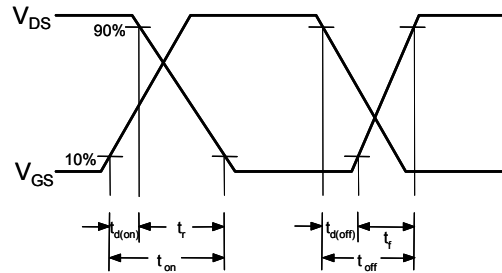
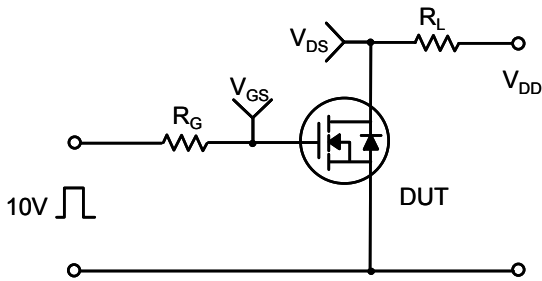
Figure 11. Transient Thermal Response Curve



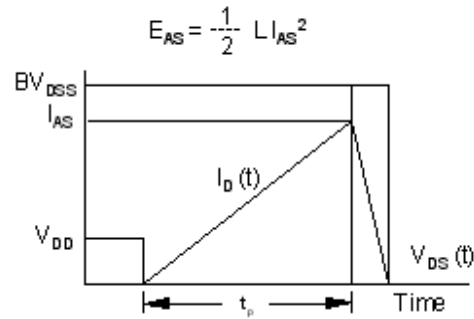
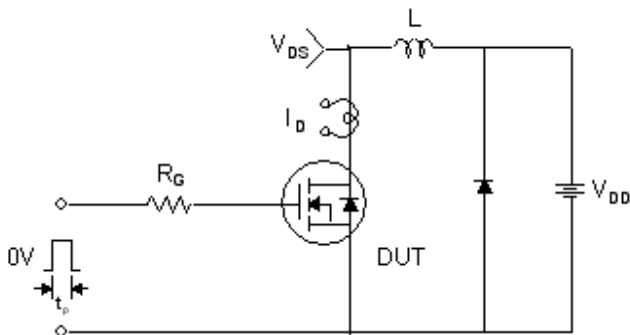
Gate Charge Test Circuit & Waveform



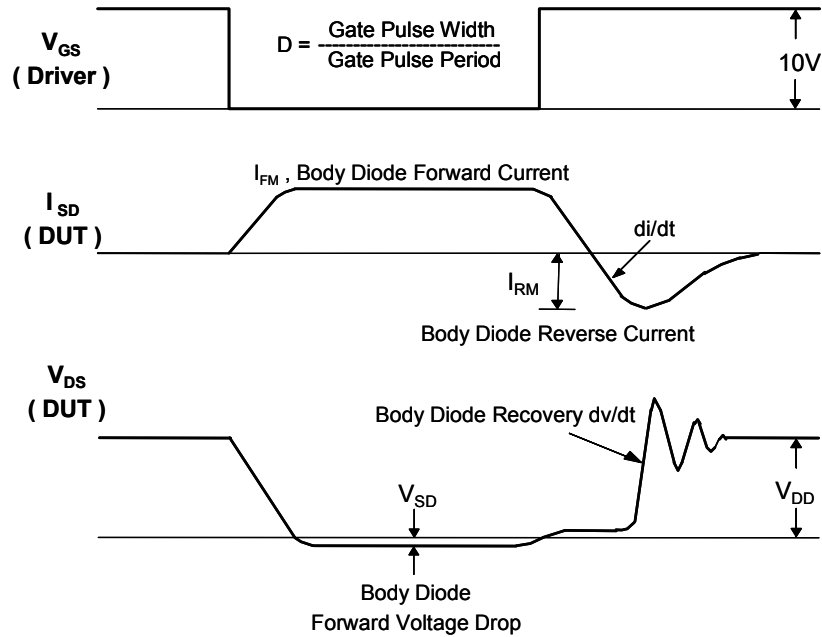
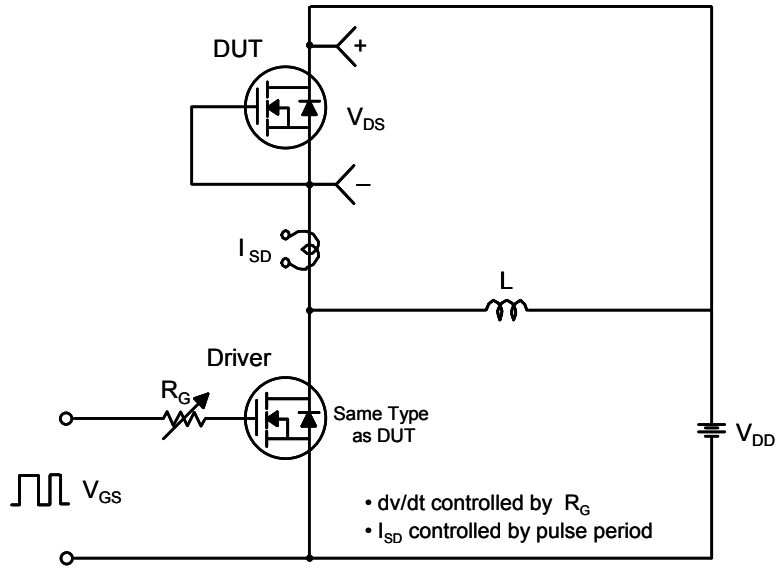
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

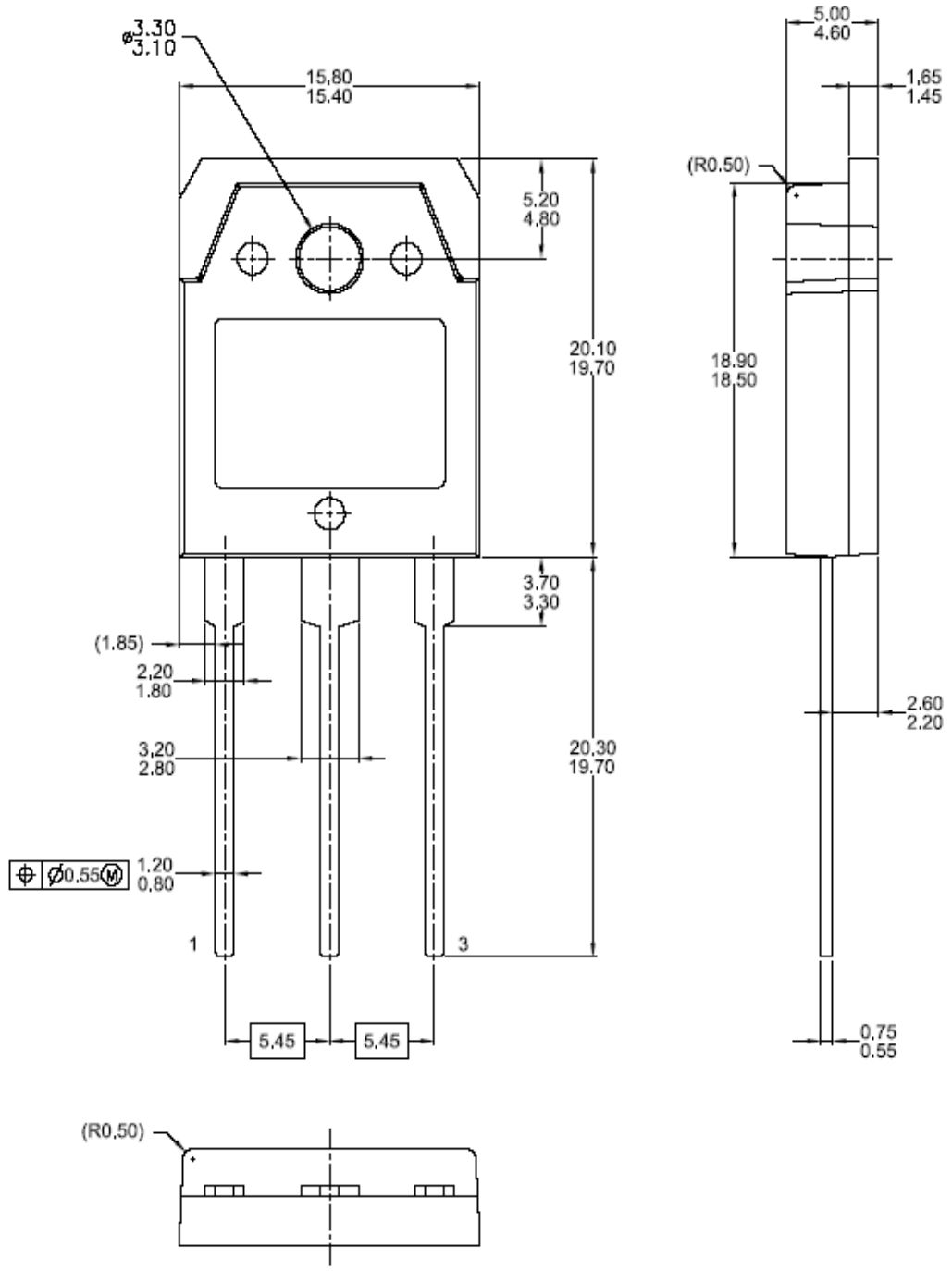


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-3PN



Dimensions in Millimeters



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